



STP80N70F6

N-channel 68 V, 0.0063 Ω typ., 96 A STripFET™ VI DeepGATE™ Power MOSFET in TO-220 package

Datasheet – production data

Features

Order code	V _{DSS} max.	R _{DS(on)} max.	I _D	P _{TOT}
STP80N70F6	68 V	< 0.008 Ω (V _{GS} = 10 V)	96 A	110 W

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- High avalanche ruggedness
- Low gate drive power losses
- Very low switching gate charge

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the 6th generation of STripFET™ DeepGATE™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

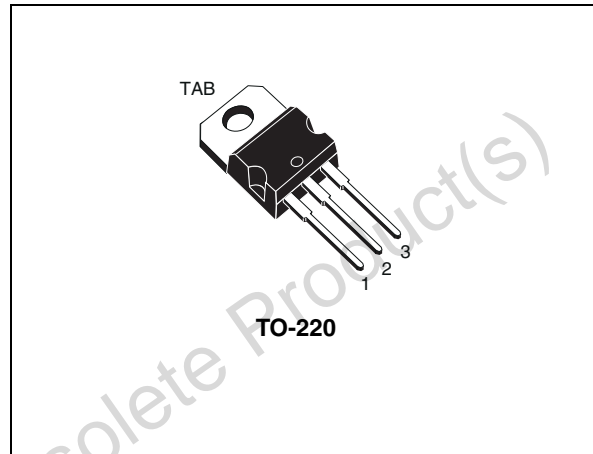


Figure 1. Internal schematic diagram

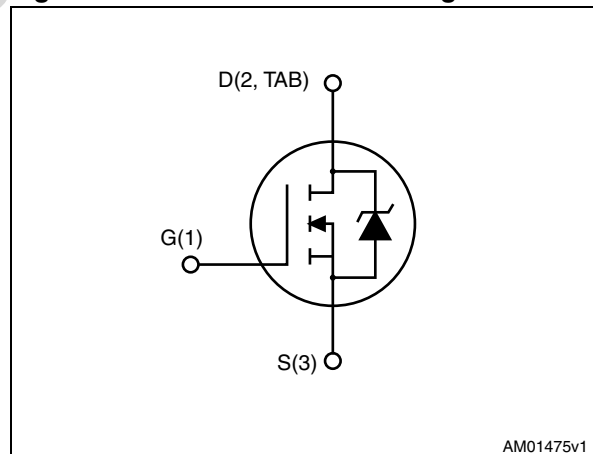


Table 1. Device summary

Order code	Marking	Package	Packaging
STP80N70F6	80N70F6	TO-220	Tube

Contents

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Obsolete Product(s) - Obsolete Product(s)

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	68	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	96	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	60	A
$I_{DM}^{(1)}$	Drain current (pulsed)	384	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
T_{stg}	Storage temperature	- 55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. This value is rated according to R_{thj-c}

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thj-c}	Thermal resistance junction-case max	1.36	$^\circ\text{C/W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C/W}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 250\ \mu A$	68			V
I_{DSS}	Zero gate voltage	$V_{DS} = 68\text{ V}$			1	μA
	Drain current ($V_{GS} = 0$)	$V_{DS} = 68\text{ V}, T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 48\text{ A}$		0.0063	0.008	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance			5850		pF
C_{oss}	Output capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	341	-	pF
C_{rss}	Reverse transfer capacitance				240	
Q_g	Total gate charge	$V_{DD} = 34\text{ V}, I_D = 96\text{ A},$ $V_{GS} = 10\text{ V}$ (see Figure 14)		99		nC
Q_{gs}	Gate-source charge			31		nC
Q_{gd}	Gate-drain charge			19		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time	$V_{DD} = 10\text{ V}, I_D = 48\text{ A},$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ (see Figure 13)	-	23	-	ns
	Rise time			29		ns
$t_{d(off)}$ t_f	Turn-off-delay time			-	102	-
	Fall time			23		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		96	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		384	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 96\text{ A}, V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 48\text{ A}, V_{DD} = 24\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s},$ $T_j = 150\text{ }^\circ\text{C}$ <i>(see Figure 15)</i>	-	34		ns
Q_{rr}	Reverse recovery charge			53		nC
I_{RRM}	Reverse recovery current			3		A

1. Pulse width is limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

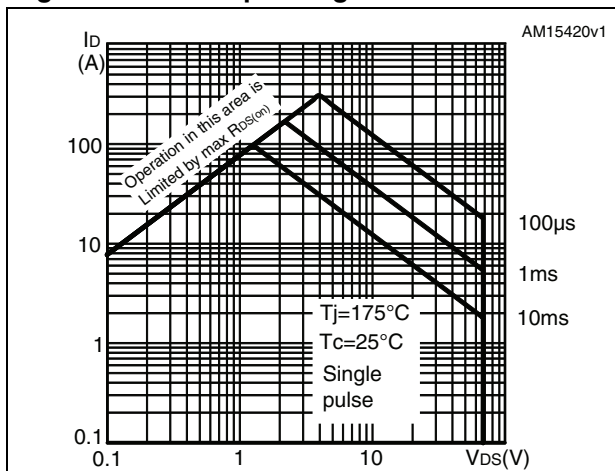


Figure 3. Thermal impedance

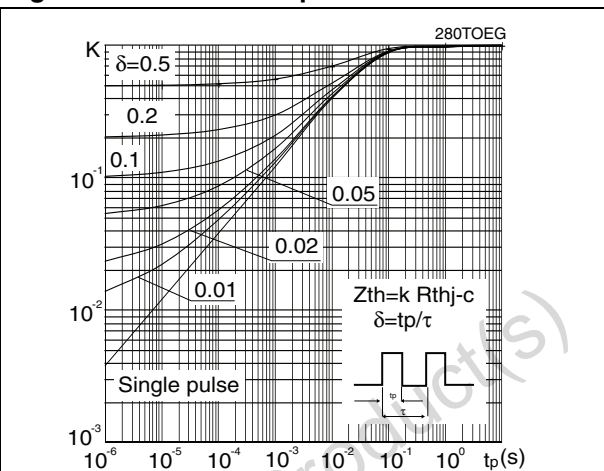


Figure 4. Output characteristics

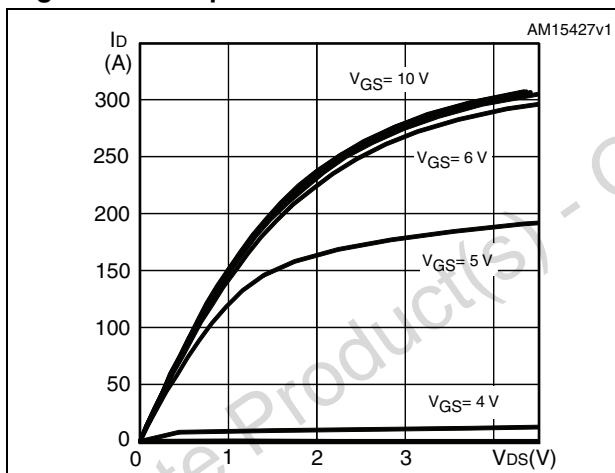


Figure 5. Transfer characteristics

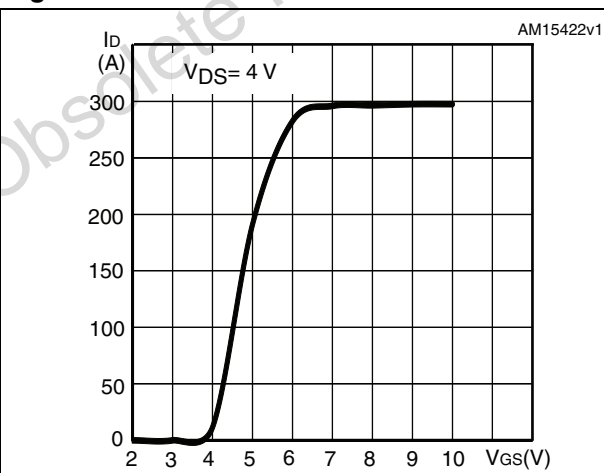


Figure 6. Gate charge vs gate-source voltage

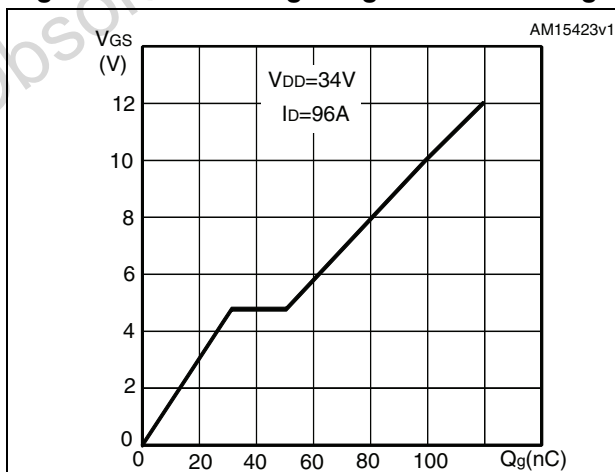


Figure 7. Static drain-source on-resistance

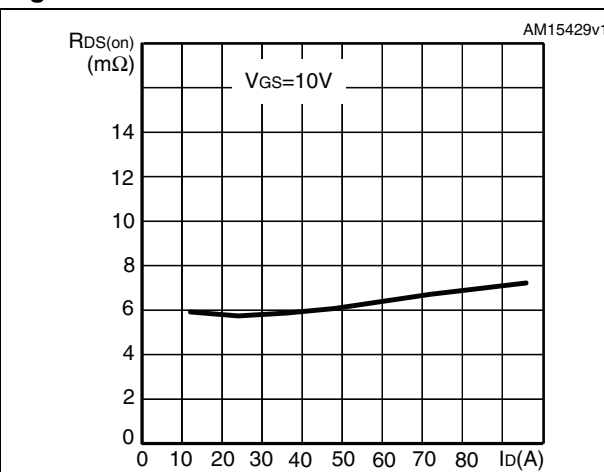


Figure 8. Capacitance variations

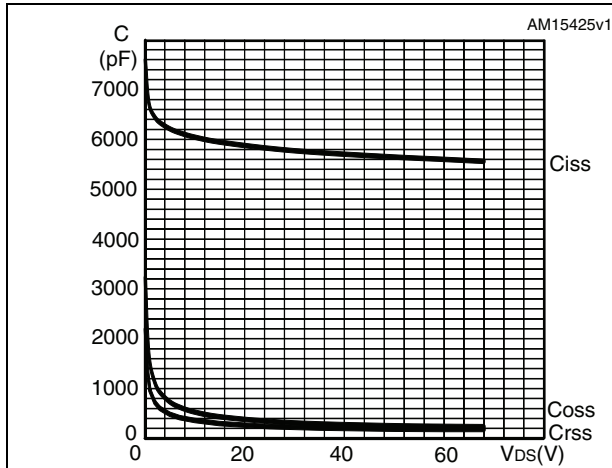


Figure 9. Normalized B_{VDSS} vs temperature

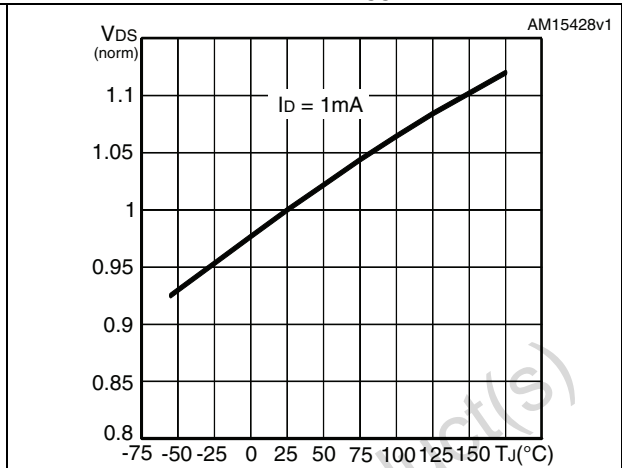


Figure 10. Normalized gate threshold voltage vs temperature

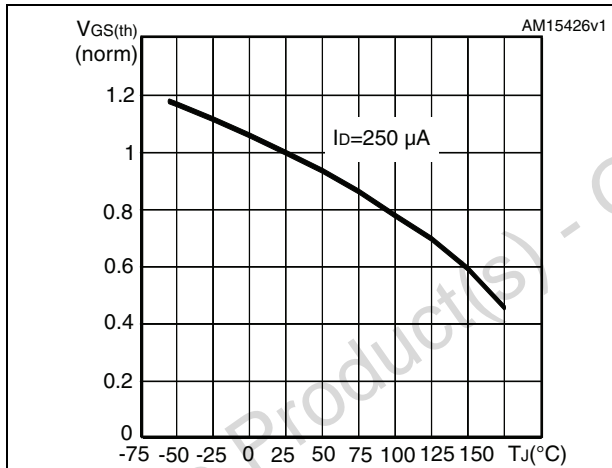


Figure 11. Normalized on-resistance vs temperature

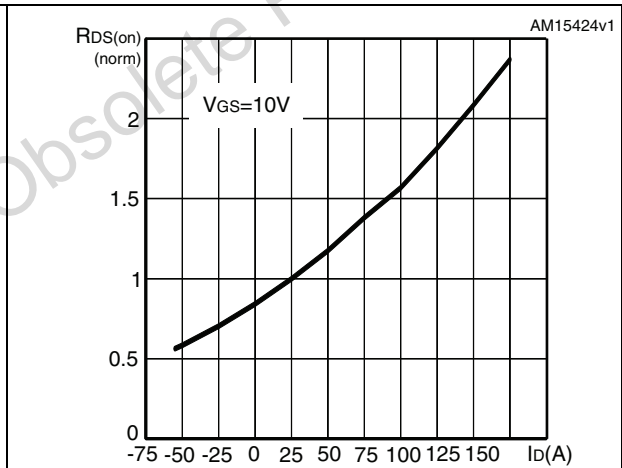
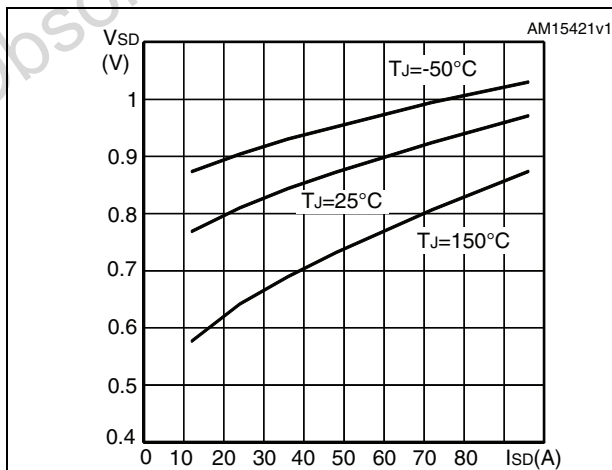
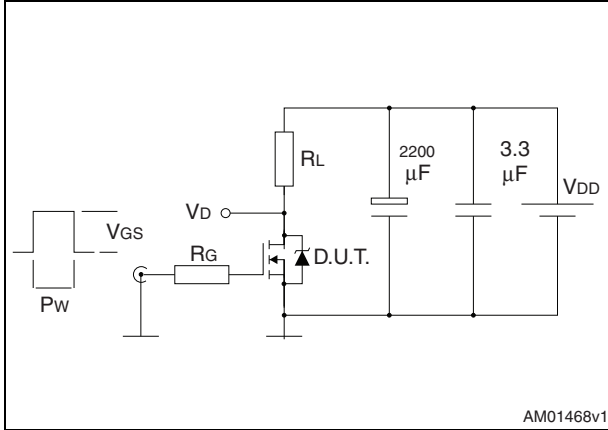


Figure 12. Source-drain diode forward characteristics



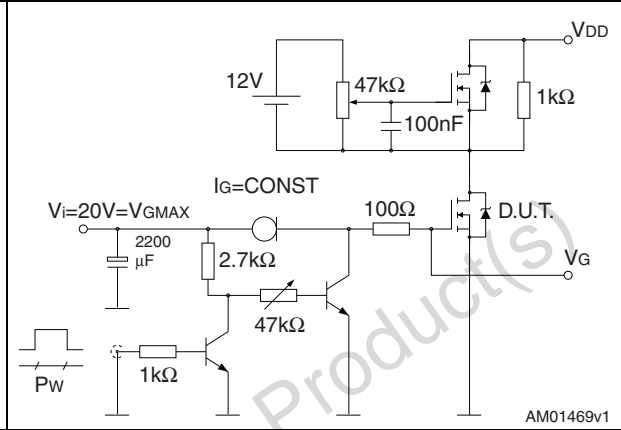
3 Test circuits

Figure 13. Switching times test circuit for resistive load



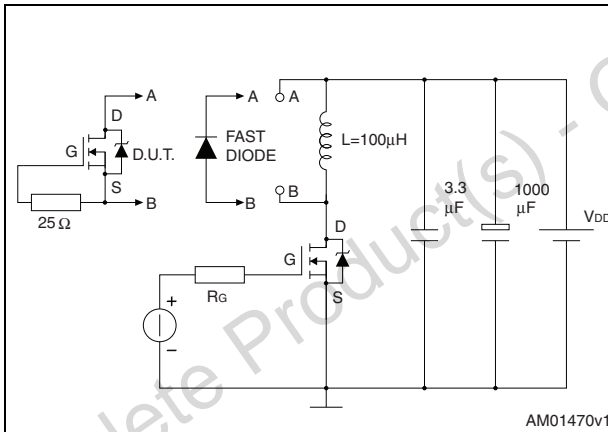
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Figure 14. Gate charge test circuit



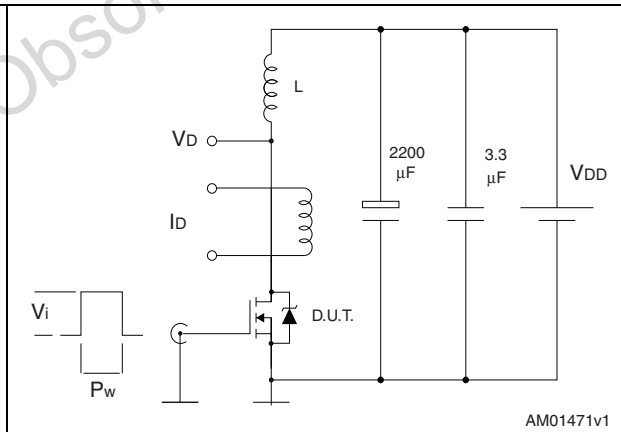
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Figure 15. Test circuit for inductive load switching and diode recovery times



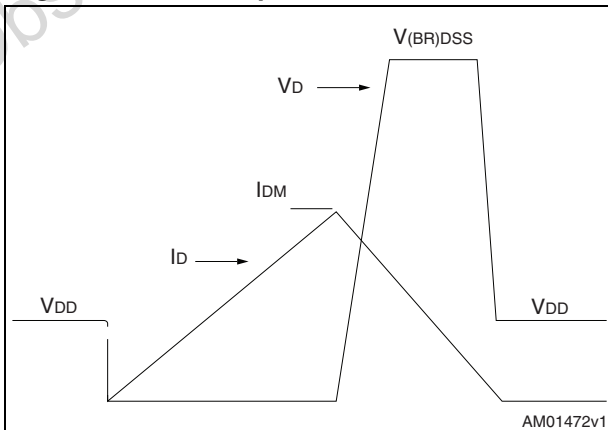
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Figure 16. Unclamped inductive load test circuit



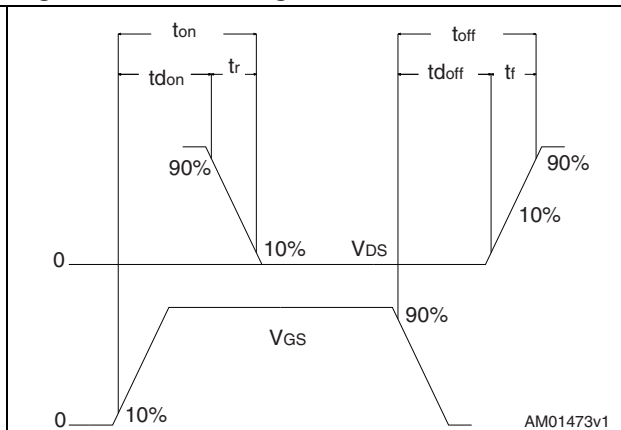
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Figure 17. Unclamped inductive waveform



AM01472v1

Figure 18. Switching time waveform



AM01473v1

4 Package mechanical data

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Table 8. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
06-Dec-2012	1	First release.

Obsolete Product(s) - Obsolete Product(s)

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